U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SNDK.327US0	10/774,014
	Applicant(s)	Conf. No.
(Use several sheets if necessary)	Gerrit Jan Hemink	8419
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	February 6, 2004	2827

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
$\mu\Gamma$	1	5,043,940	8/27/1991	Harari			
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Foreign Patent Documents

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

$\mu\Gamma$	12	Takaaki Nozaki et al., "A 1-Mb EEPROM with MONOS Memory Cell for Semiconductor Disk Application" IEEE Journal of Solid-State Circuits, Vol. 26, No. 4, April 1991, pp. 497-501.
	13	K. D. Suh et al. in "A 3.3 V 32 Mb NAND Flash Memory with Incremental Step Pulse Programming Scheme," Journal of Solid-State Circuits, Vol 30, No. 11, Nov. 1995, pp. 1149-55.
$\mu\Gamma$	14	T. S. Jung et al. proposed a local self boosting ("LSB") technique in "A 3.3V 128Mb Multi-Level NAND Flash Memory for Mass Storage Applications", ISSCC96, Session 2, Flash Memory, Paper TP 2.1, IEEE, pp. 32.

Examiner	M. TRAN	Date Considered	6/9/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.